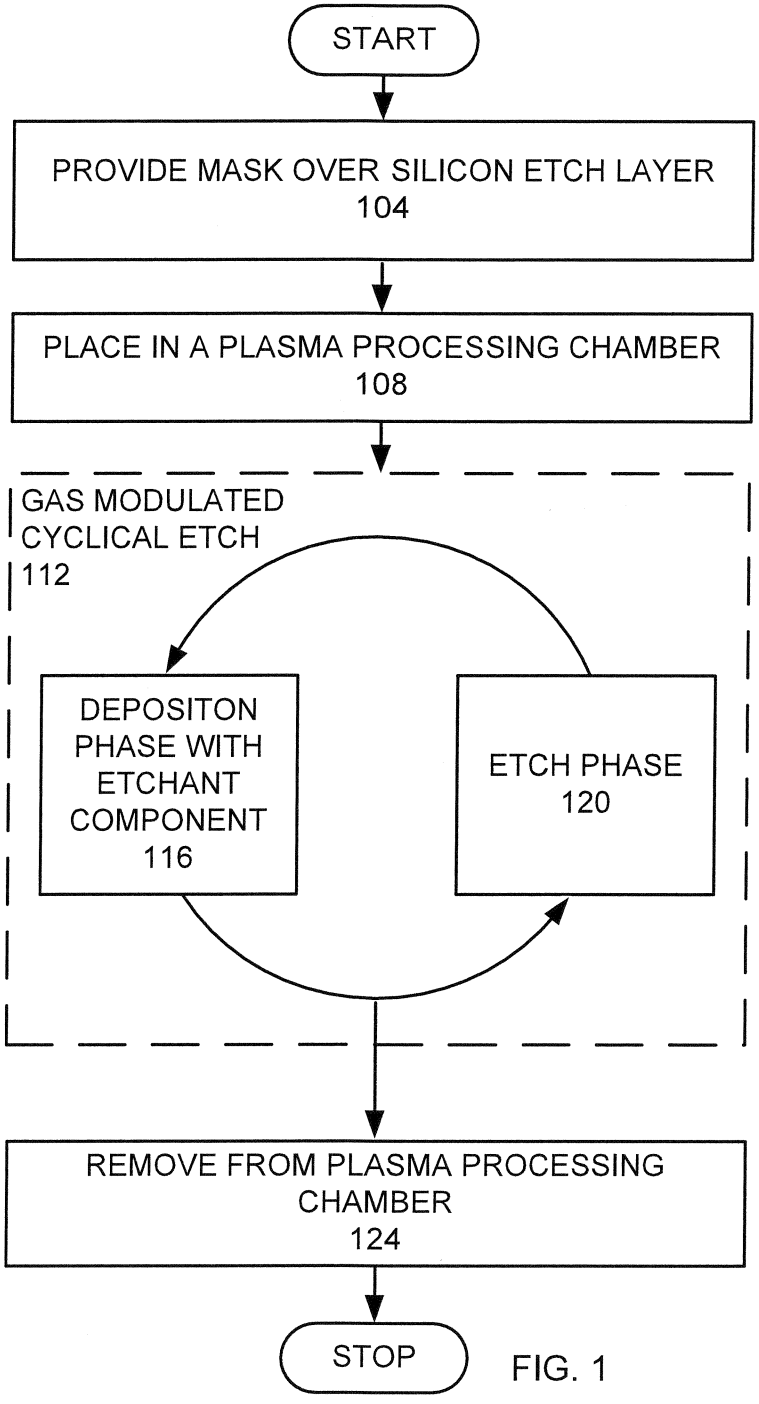

START
PROVIDE MASK OVER SILICON ETCH LAYER
104
PLACE IN A PLASMA PROCESSING CHAMBER
108
GAS MODULATED
CYCLICAL ETCH
112
DEPOSITON
PHASE WITH
ETCHANT
COMPONENT
116
ETCH PHASE
120
REMOVE FROM PLASMA PROCESSING
CHAMBER
124
STOP

FIG. 1

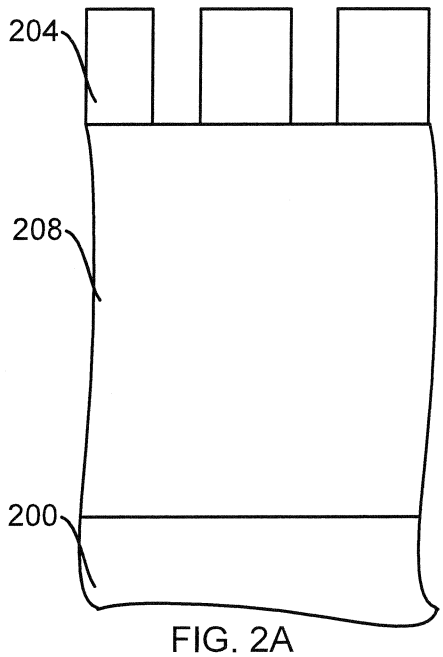


FIG. 2A

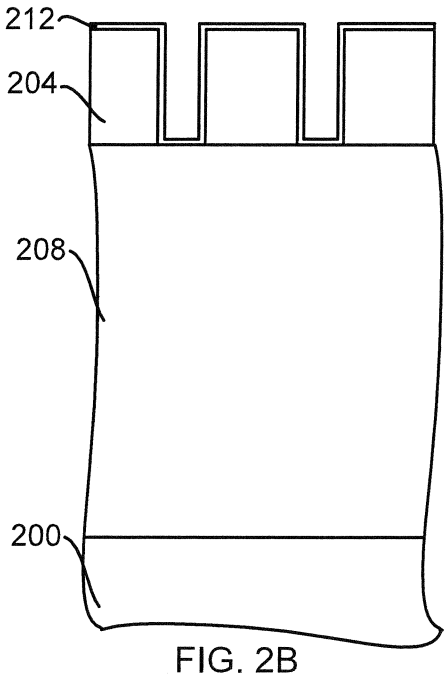


FIG. 2B

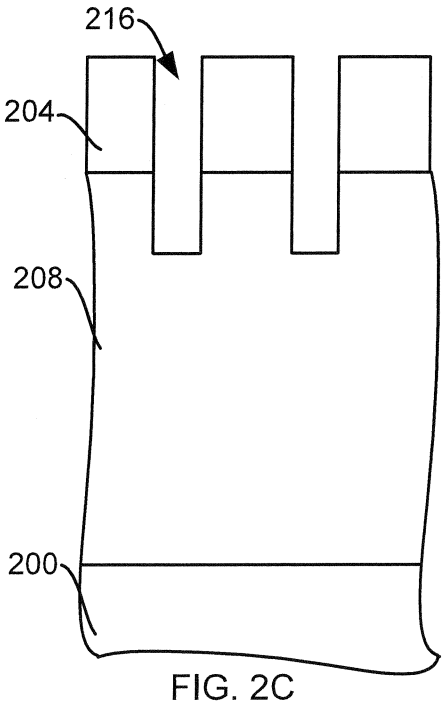


FIG. 2C

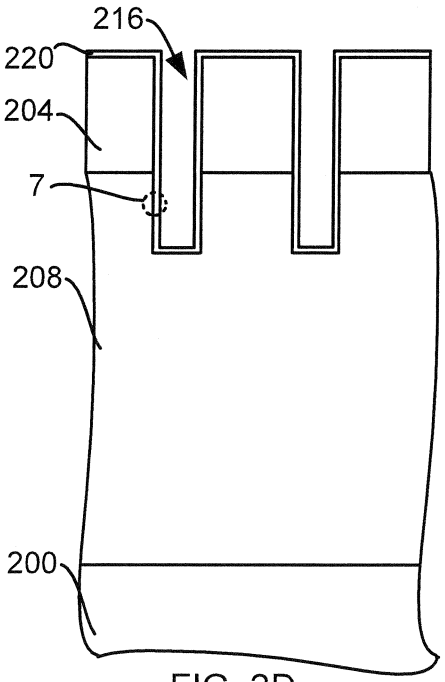


FIG. 2D

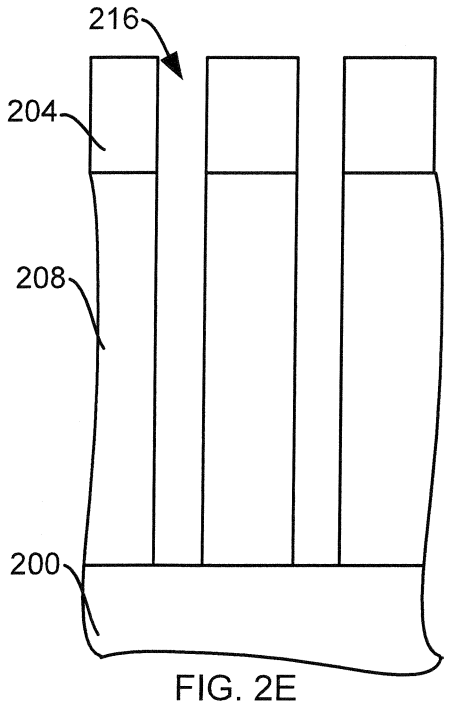


FIG. 2E

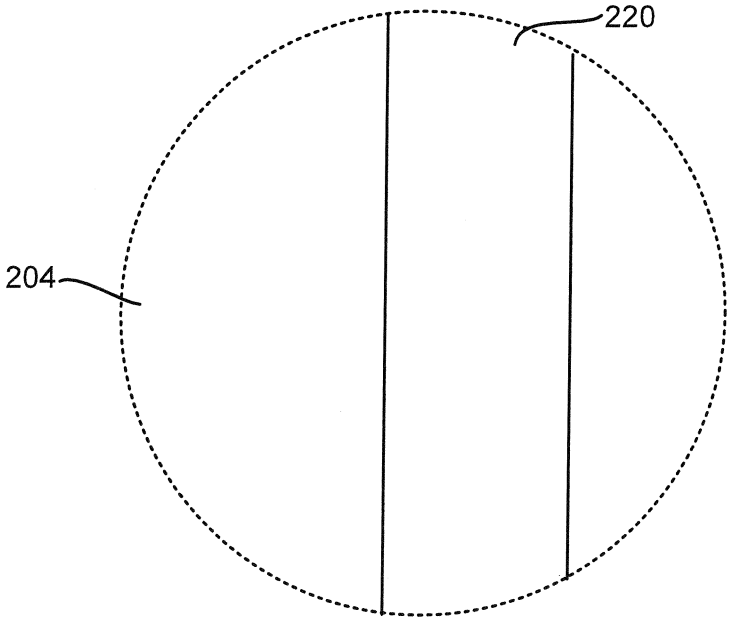


FIG. 7

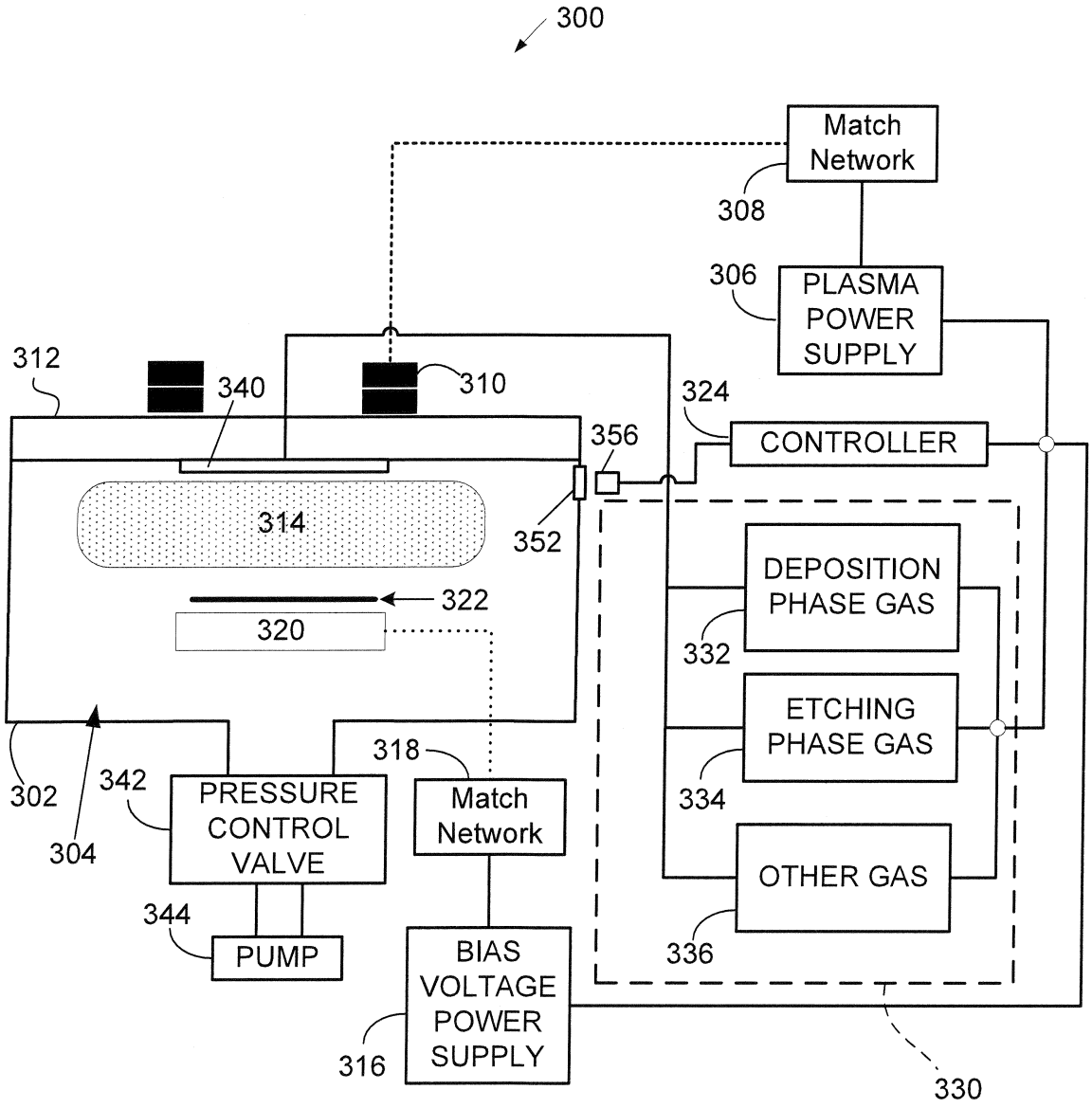

300
Match Network
308
306
PLASMA POWER SUPPLY
312
340
310
324
CONTROLLER
356
314
352
DEPOSITION PHASE GAS
322
320
332
ETCHING PHASE GAS
318
334
302
342
PRESSURE CONTROL VALVE
Match Network
304
OTHER GAS
344
336
PUMP
BIAS VOLTAGE POWER SUPPLY
316
330

FIG. 3

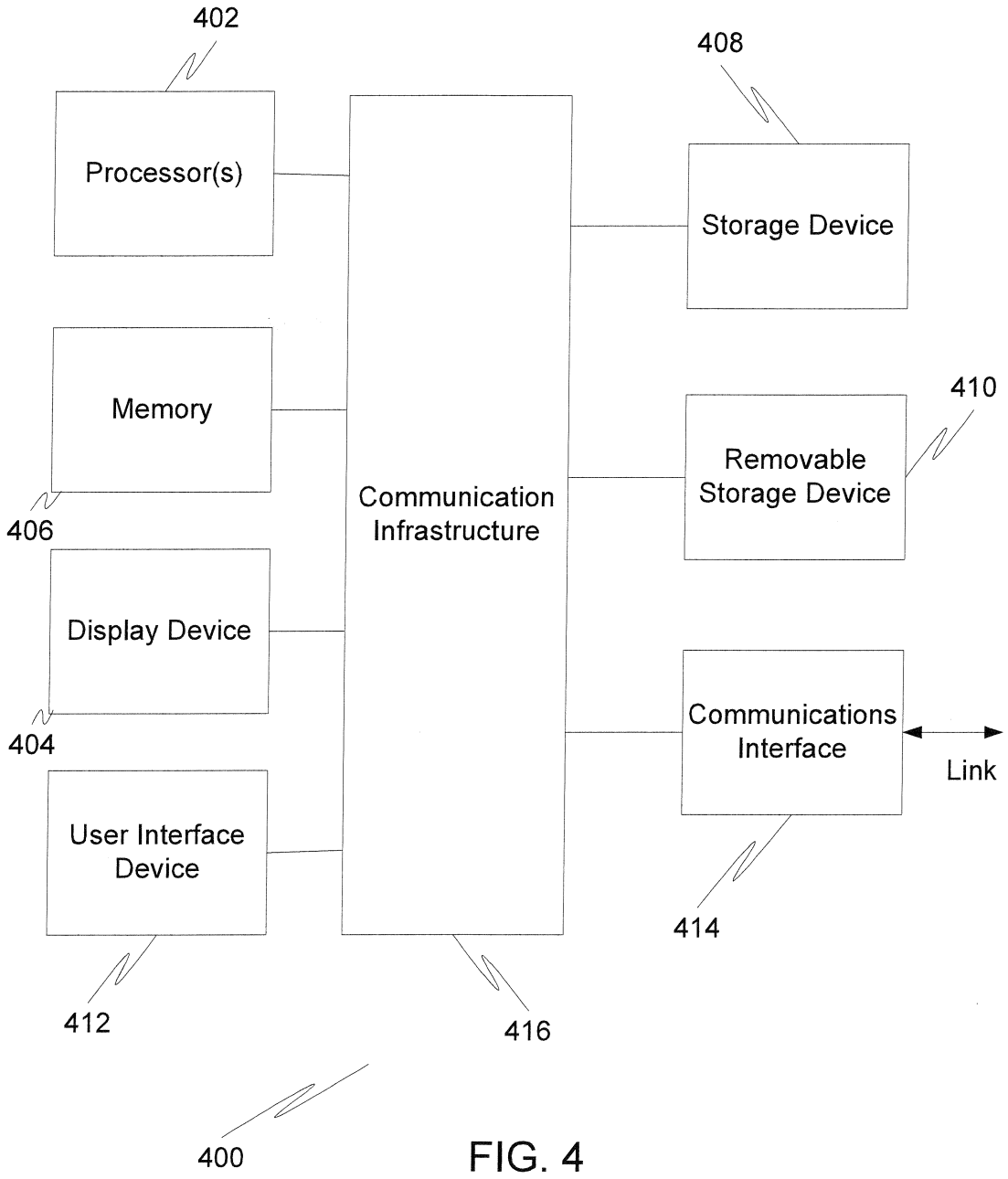

402
Processor(s)
408
Storage Device
Memory
406
Communication Infrastructure
410
Removable Storage Device
Display Device
404
Communications Interface
Link
User Interface Device
414
412
416
400

FIG. 4

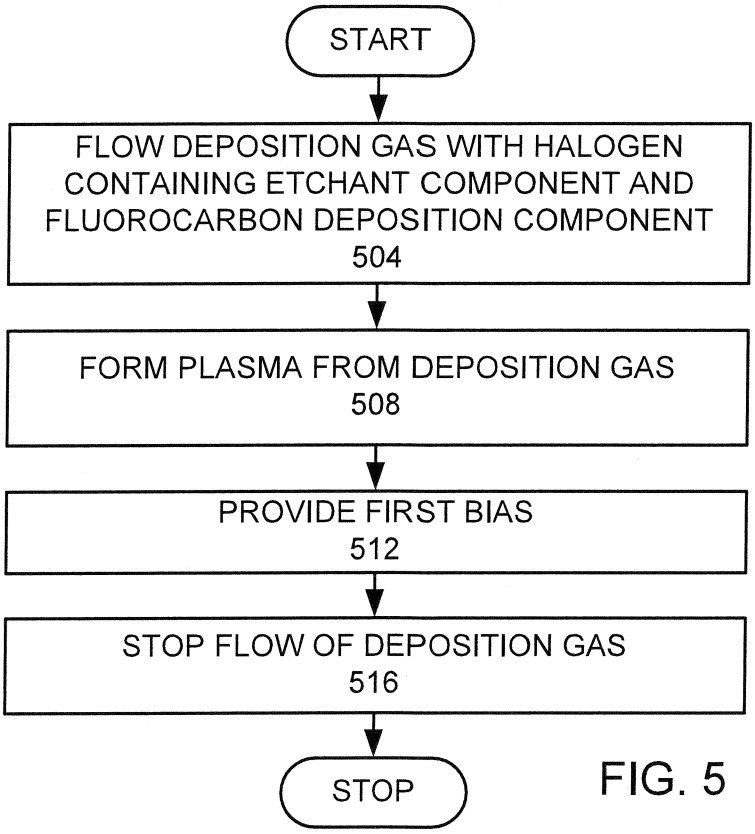

START
FLOW DEPOSITION GAS WITH HALOGEN CONTAINING ETCHANT COMPONENT AND FLUOROCARBON DEPOSITION COMPONENT
504
FORM PLASMA FROM DEPOSITION GAS
508
PROVIDE FIRST BIAS
512
STOP FLOW OF DEPOSITION GAS
516
STOP

FIG. 5

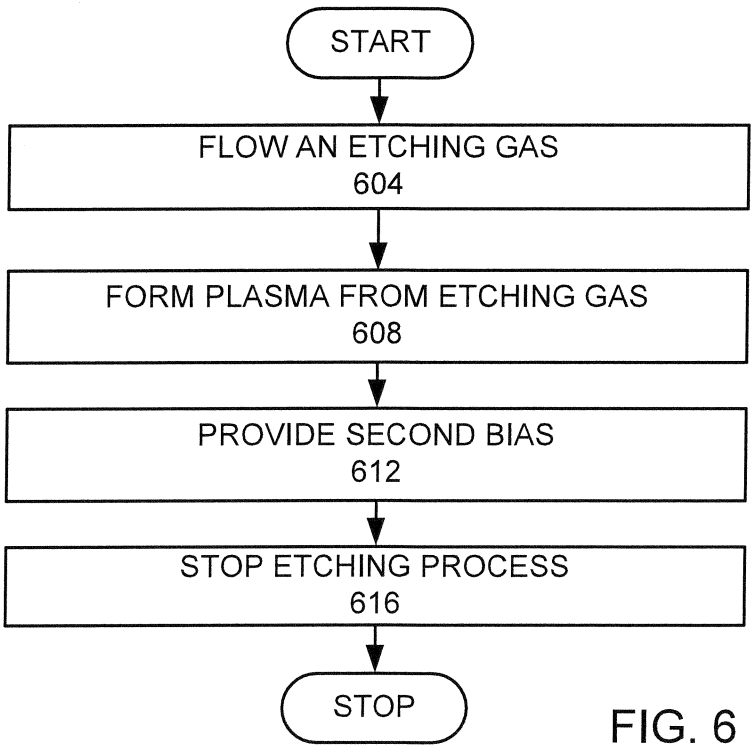

START
FLOW AN ETCHING GAS
604
FORM PLASMA FROM ETCHING GAS
608
PROVIDE SECOND BIAS
612
STOP ETCHING PROCESS
616
STOP

FIG. 6

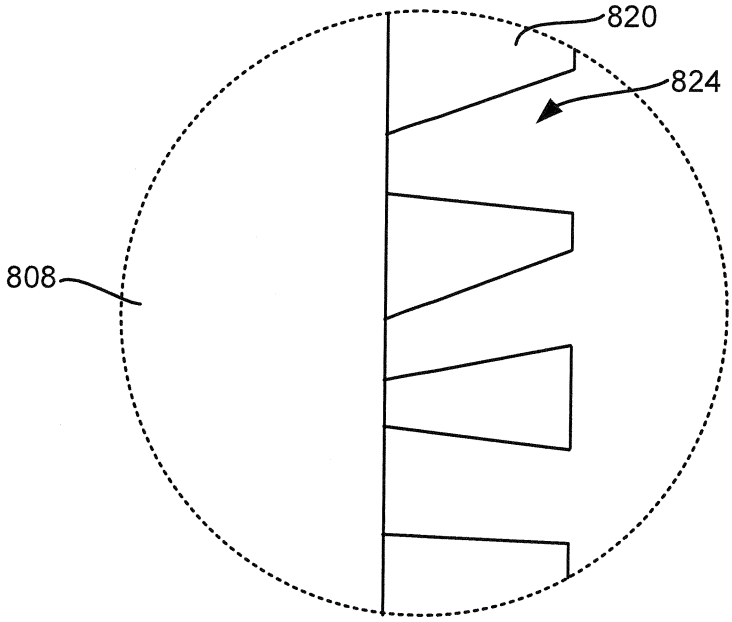


FIG. 8A (PRIOR ART)

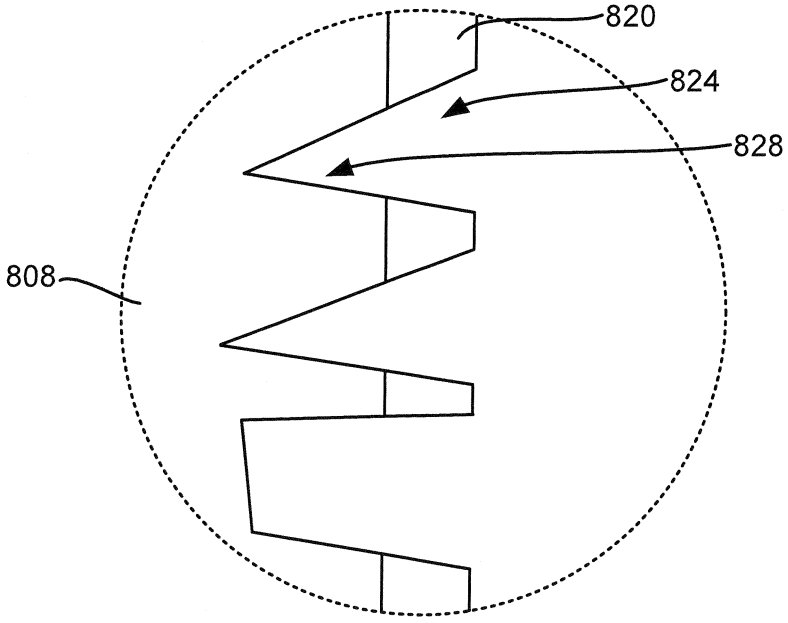


FIG. 8B (PRIOR ART)

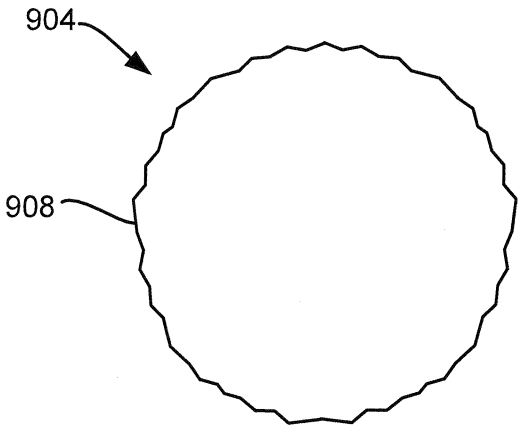


FIG. 9A (PRIOR ART)

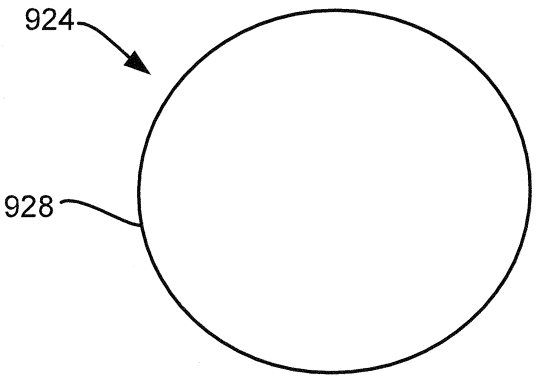


FIG. 9B